

**RoHS** 

COMPLIANT

HALOGEN

FREE Available

Vishay Siliconix

## N-Channel 20-V (D-S) MOSFET

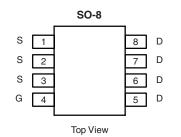
PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$V_{DS}(V)$ $R_{DS(on)}(\Omega)$			
20	0.0035 at $V_{GS}$ = 4.5 V	25		
	0.0047 at V <sub>GS</sub> = 2.5 V	20		

## **FEATURES**

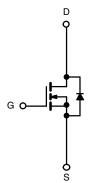
- Halogen-free According to IEC 61249-2-21
  Available
- TrenchFET<sup>®</sup> Power MOSFETs: 2.5 V Rated
- Low 3.5 mΩ R<sub>DS(on)</sub>
  - PWM ( $Q_{gd}$  and  $R_{g}$ ) Optimized

### **APPLICATIONS**

 Low-Side MOSFET in Synchronous Buck DC/DC Converters in Servers and Routers



Ordering Information: Si4864DY-T1-E3 (Lead (Pb)-free) Si4864DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b> $T_A = 25 \degree C$ , unless otherwise noted						
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V <sub>DS</sub>	20		V	
Gate-Source Voltage		V <sub>GS</sub>	± 8		v	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 25 °C	– I <sub>D</sub>	25	17		
	T <sub>A</sub> = 70 °C		20	13		
Pulsed Drain Current (10 µs Pulse Width)		I <sub>DM</sub>	60		A	
Continuous Source Current (Diode Conduction) <sup>a</sup>		۱ <sub>S</sub>	2.9	1.3		
	T <sub>A</sub> = 25 °C	PD	3.5 1.6		W	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C	'D	2.2	1	vv	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 1	to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
	t ≤ 10 s	R <sub>thJA</sub>	29	35		
Maximum Junction-to-Ambient <sup>a</sup>	Steady State		67	80	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	13	16		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static			•	•		
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	0.6		2	V
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V$ , $V_{GS} = \pm 8 V$			± 100	nA
Zero Gate Voltage Drain Current		$V_{DS} = 20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$ $V_{DS} = 20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 55 \text{ °C}$			1	μΑ
	IDSS				5	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \geq 5$ V, $V_{GS}$ = 4.5 V	30			А
Drain-Source On-State Resistance <sup>a</sup>				0.0028	0.0035	Ω
	R <sub>DS(on)</sub>			0.0038	0.0047	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = 6 V, I_{D} = 25 A$		70		S
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	$I_{S} = 2.9 \text{ A}, V_{GS} = 0 \text{ V}$		0.70	1.1	V
Dynamic <sup>b</sup>	1 1					
Total Gate Charge	Qg			47	70	
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ = 10 V, $V_{GS}$ = 4.5 V, $I_D$ = 25 A		10		nC
Gate-Drain Charge	Q <sub>gd</sub>			13.4		
Gate Resistance	Rg		0.5	1.5	2.6	Ω
Turn-On Delay Time	t <sub>d(on)</sub>			40	60	
Rise Time	t <sub>r</sub>	$V_{DD}$ = 10 V, $R_L$ = 10 $\Omega$		44	65	
Turn-Off Delay Time	t <sub>d(off)</sub>	$\text{I}_\text{D}\cong \text{1}$ A, $\text{V}_\text{GEN}$ = 4.5 V, $\text{R}_\text{g}$ = 6 $\Omega$		150	240	ns
Fall Time	t <sub>f</sub>			72	110	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 2.9 A, dl/dt = 100 A/μs		57	80	

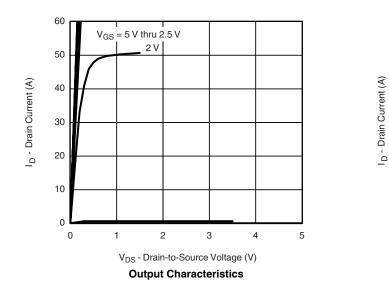
Notes:

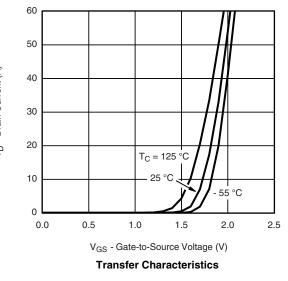
a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

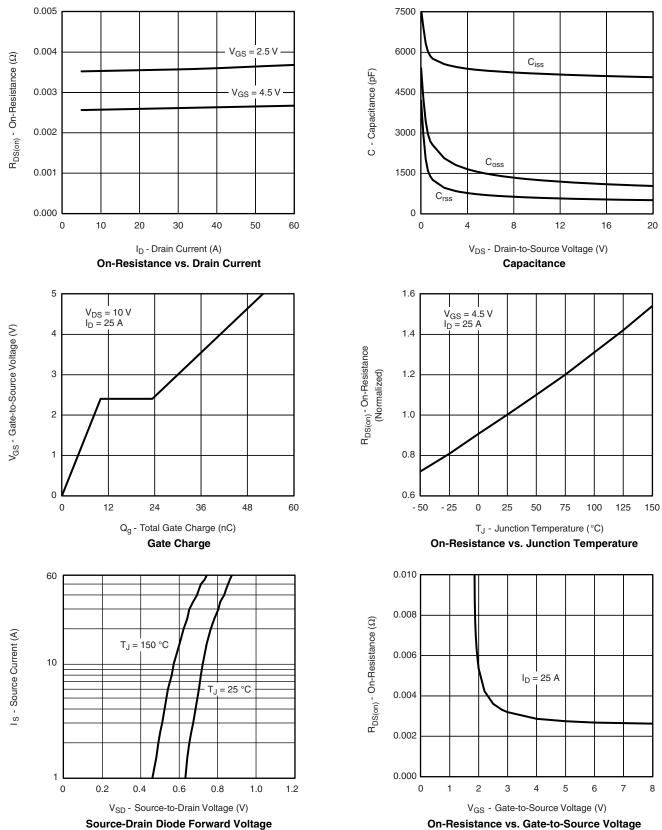




Si4864DY Vishay Siliconix



VISHAY



Document Number: 71449 S09-0221-Rev. C, 09-Feb-09

## Si4864DY

## **Vishay Siliconix**

#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted 0.4 60 0.2 50 $I_D = 250 \ \mu A$ 0.0 V<sub>GS(th)</sub> Variance (V) 40 Power (W) - 0.2 30 - 0.4 20 - 0.6 10 - 0.8 - 1.0 0 -50 - 25 50 0 25 75 100 125 150 10<sup>-2</sup> 10<sup>-1</sup> 10 100 1 T<sub>J</sub> - Temperature (°C) Time (s) **Threshold Voltage** Single Pulse Power 2 1 Normalized Effective Transient Thermal Impedance Duty Cycle = 0.5 TT 0.2 Notes 4 0.1 PDN 0.1 0.05 t<sub>1</sub> t; $\square$ t<sub>1</sub> 1. Duty Cycle, D = t<sub>2</sub> 0.02 2. Per Unit Base = R<sub>thJA</sub> = 67 °C/W 3. T<sub>JM</sub> - T<sub>A</sub> = $P_{DM}Z_{thJA}^{(t)}$ Single Pulse 4. Surface Mounted 0.01 10-4 10<sup>-3</sup> 10<sup>-2</sup> 10-1 10 100 600 1 Square Wave Pulse Duration (s) Normalized Thermal Transient Impedance, Junction-to-Ambient 2 1 Normalized Effective Transient Thermal Impedance Duty Cycle = 0.5 0.2 0.1 0.1 0.05 0.02 Single Pulse 0.01

Square Wave Pulse Duration (s) Normalized Thermal Transient Impedance, Junction-to-Foot

10

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <u>www.vishay.com/ppg?71449</u>.

10-2

10-4

10<sup>-3</sup>

1

10



600



# Package Information

Vishay Siliconix

# SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012





	MILLIM	IETERS	INC	HES		
DIM	Min	Мах	Min	Max		
A	1.35	1.75	0.053	0.069		
A <sub>1</sub>	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
E	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498						

# **Application Note 826**

Vishay Siliconix



**RECOMMENDED MINIMUM PADS FOR SO-8** 



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



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